

WORCESTER POLYTECHNIC INSTITUTE MECHANICAL ENGINEERING DEPARTMENT

Engineering Experimentation
ME-3901, A'2010

Lecture 12

06 October 2010



General information

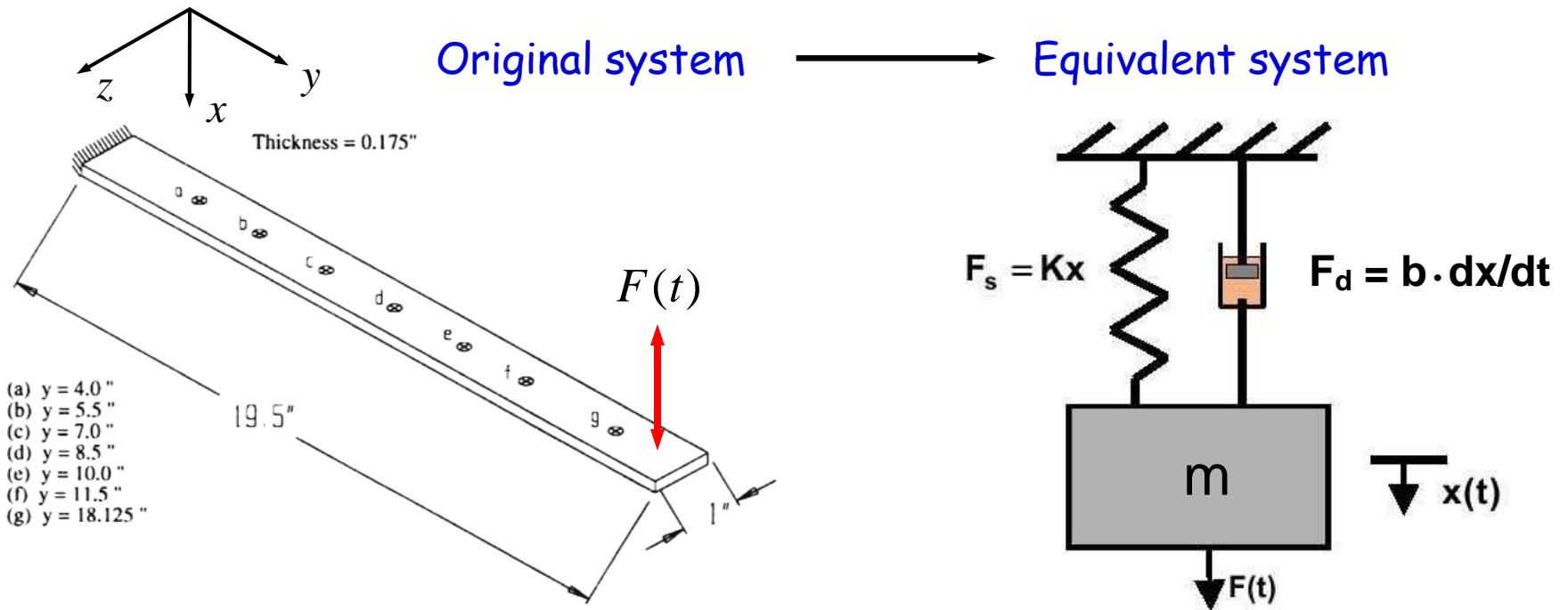
Office hours

Instructor: Cosme Furlong; cfurlong@wpi.edu
Everyday from 11:00 to 11:50 am
or by appointment

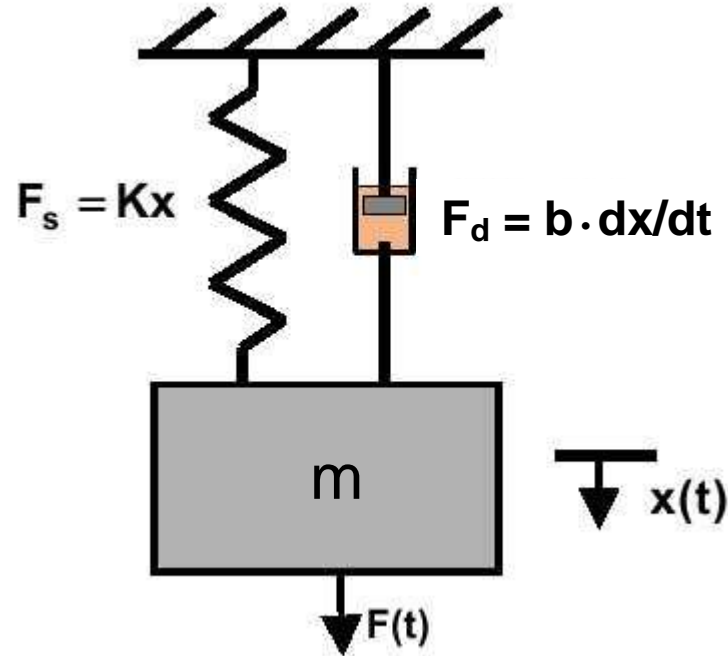
Teaching Assistant: Jeffrey Laut & Kazim Naqvi;
During Lab Sessions



Equivalent systems



Analysis of a single degree of freedom system



Governing equation:
$$m \frac{d^2 x}{dt^2} = \sum_i F_i$$

$$m \frac{d^2 x}{dt^2} = -kx - b \frac{dx}{dt} + F(t)$$

← External force



Analysis of a single degree of freedom system

First case: $F(t) \neq 0$ – Forced vibrations

Governing equation:
$$m \frac{d^2 x}{dt^2} + b \frac{dx}{dt} + kx = F(t)$$

Governing equation can be written as:

$$\frac{d^2 x}{dt^2} + \frac{b}{m} \frac{dx}{dt} + \frac{k}{m} x = \frac{F(t)}{m} \quad \longrightarrow \quad \frac{d^2 x}{dt^2} + 2\lambda \frac{dx}{dt} + \omega^2 x = F'(t)$$

Solution has the form:

$$x(t) = x_c(t) + x_p(t)$$

$x_c(t)$ Complementary solution

$x_p(t)$ Particular solution

Solution requires the method of *undetermined coefficients*



Analysis of a single degree of freedom system

First case: $F(t) \neq 0$ – Forced vibrations

Governing equation: $\rightarrow \frac{d^2 x}{dt^2} + 2\lambda \frac{dx}{dt} + \omega^2 x = F_o \sin(\gamma t)$

Solution has the form: $x(t) = x_c(t) + x_p(t)$

$$x(t) = \underbrace{Ae^{-\lambda t} \sin(\sqrt{\omega^2 - \lambda^2} t + \phi)}_{\text{transient}} + \underbrace{\frac{F_o}{\sqrt{(\omega^2 - \lambda^2)^2 + 4\lambda^2 \gamma^2}} \sin(\gamma t + \theta)}_{\text{steady state}}$$

with: $\sin(\phi) = \frac{C_1}{A}$; $\sin(\theta) = \frac{-2\lambda\gamma}{\sqrt{(\omega^2 - \lambda^2)^2 + 4\lambda^2 \gamma^2}}$

$\cos(\phi) = \frac{C_2}{A}$; $\cos(\theta) = \frac{\omega^2 - \lambda^2}{\sqrt{(\omega^2 - \lambda^2)^2 + 4\lambda^2 \gamma^2}}$



Analysis of a single degree of freedom system

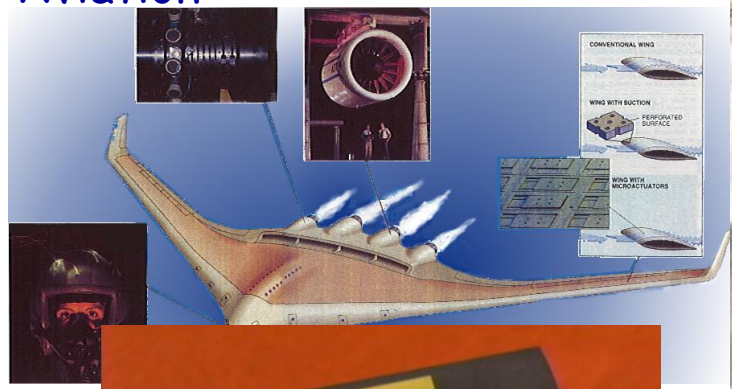
First case: $F(t) \neq 0$ – Forced vibrations

REVIEW - Lecture 10: section on accelerometers

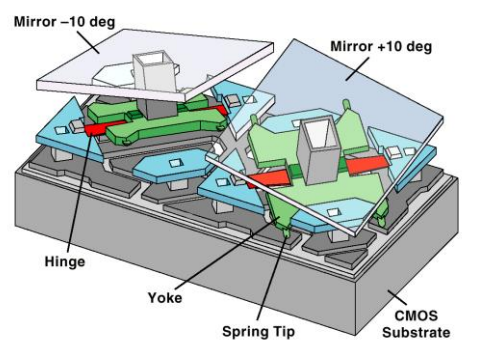
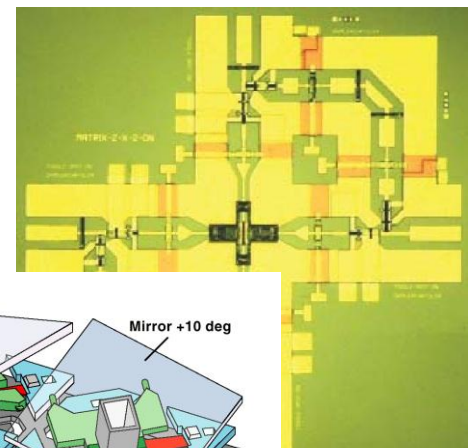


MEMS sensors & actuators: some applications

Aviation



Microelectronics: RF MEMS



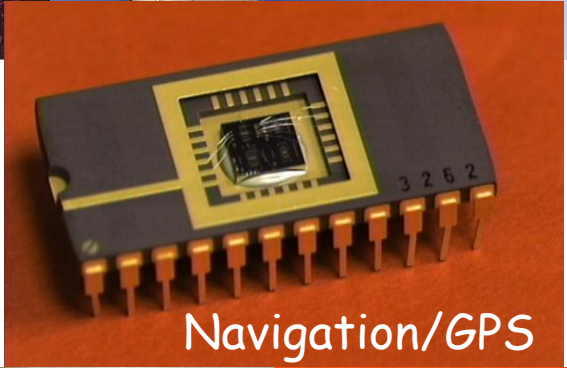
Photonics



Tele-com



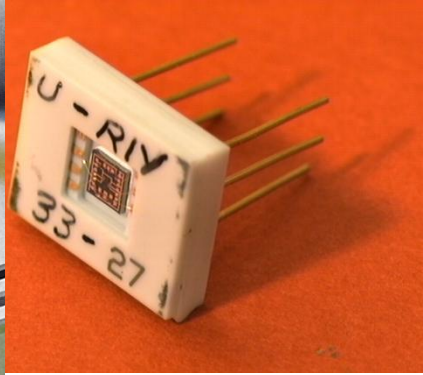
Segway: sensors



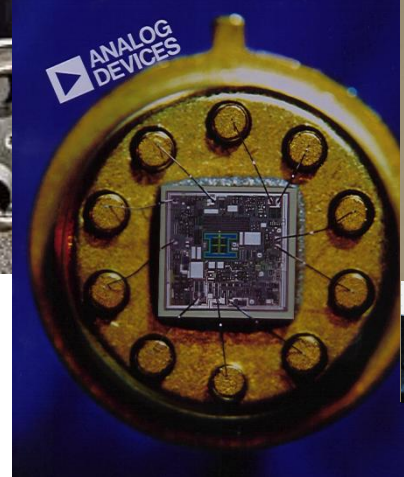
Navigation/GPS



Info-tech



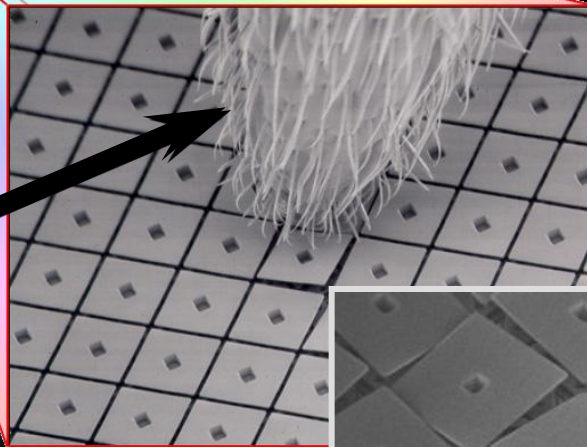
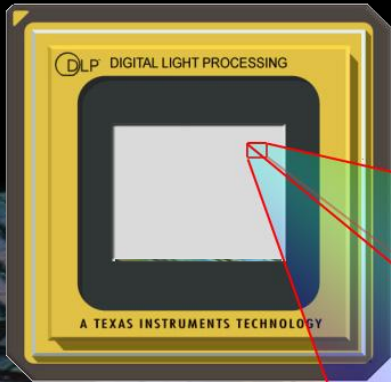
Controls



Automotive

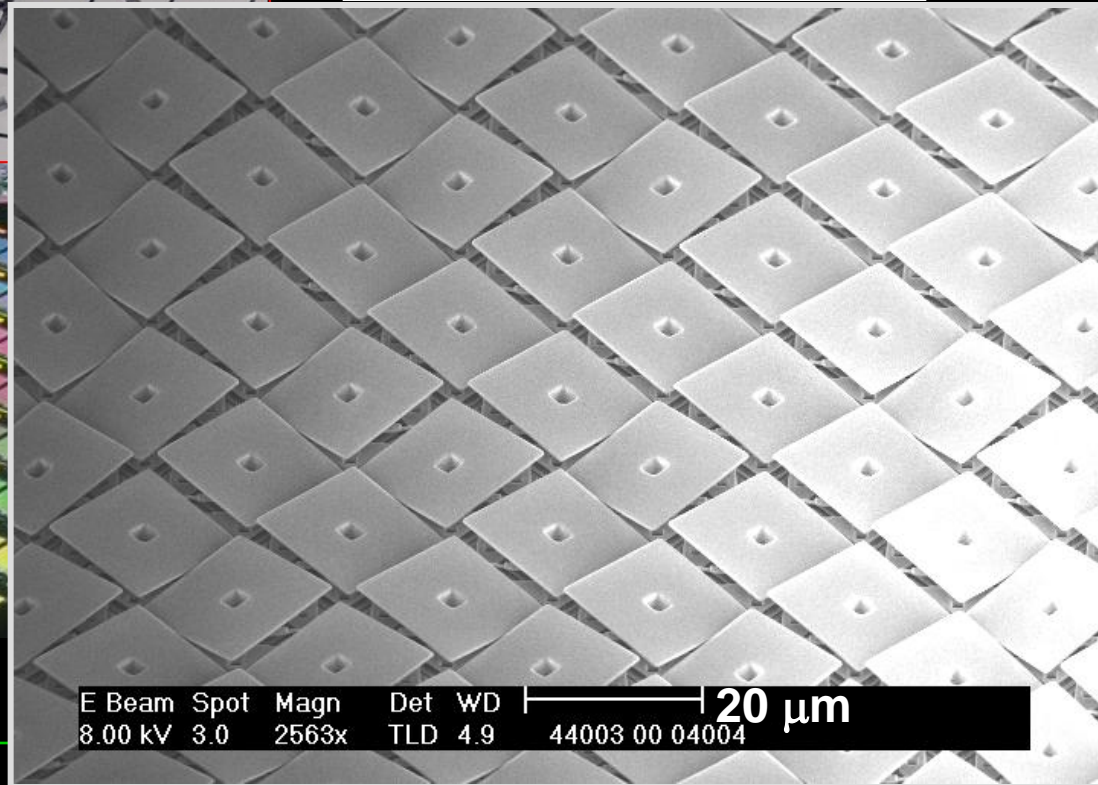


The Digital Micromirror Device



Ants Foot

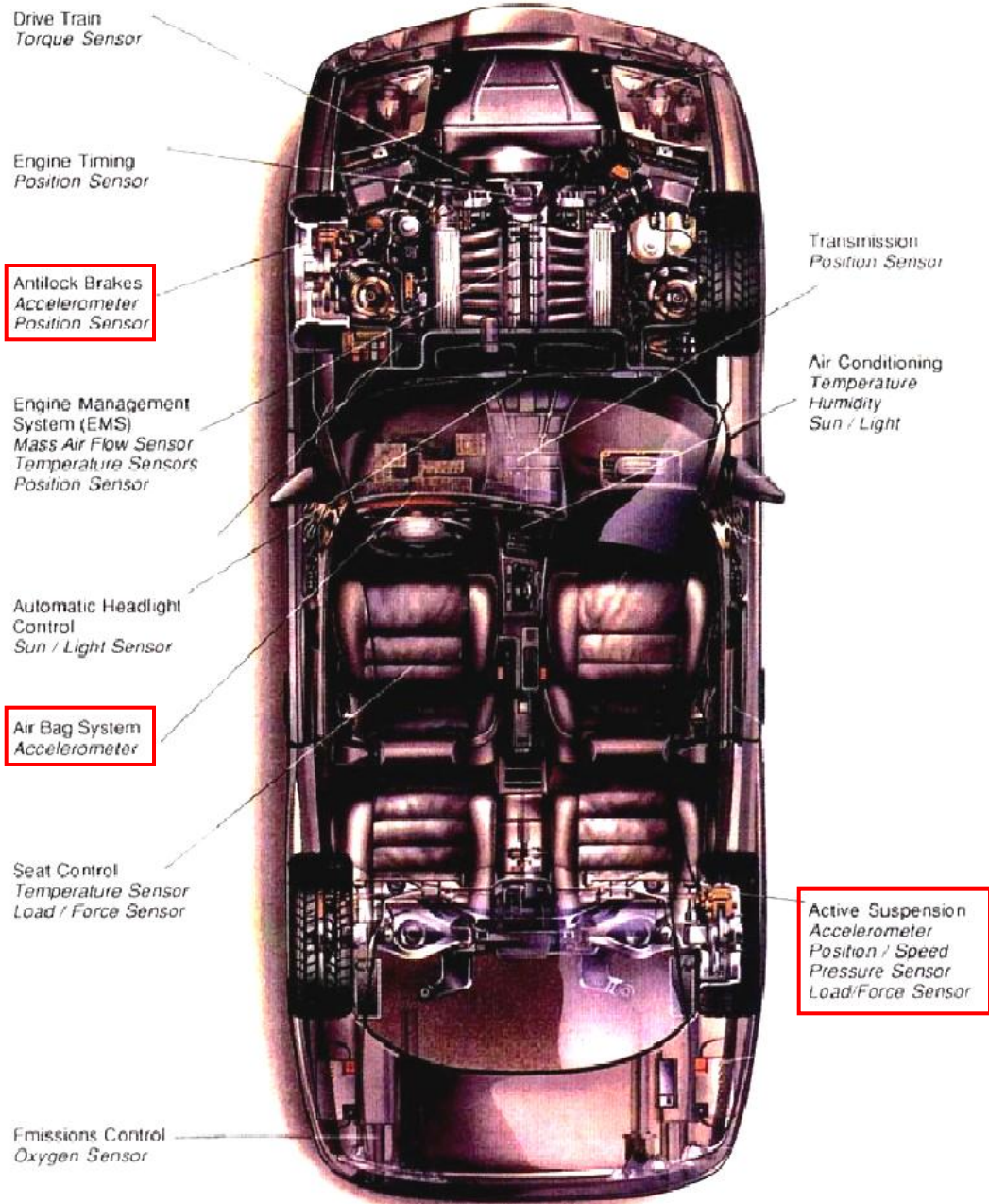
Close-up of Chip Surface



<http://www.dlp.com/>

MEMS sensors: some applications

(MEMS - Microelectromechanical Systems)

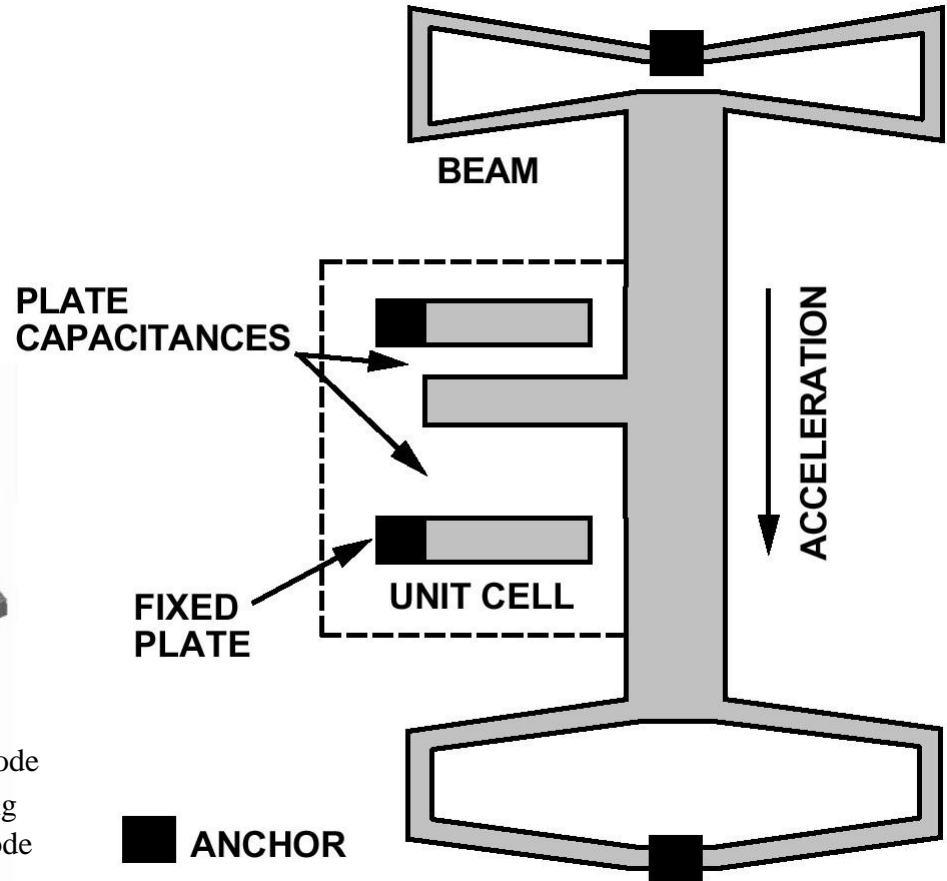
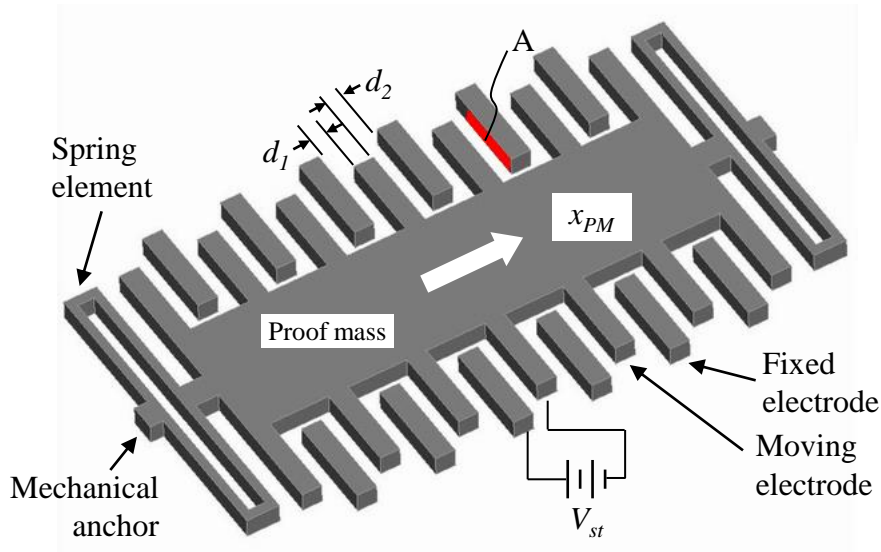


MEMS accelerometers

Simplified view of a sensor subjected to acceleration

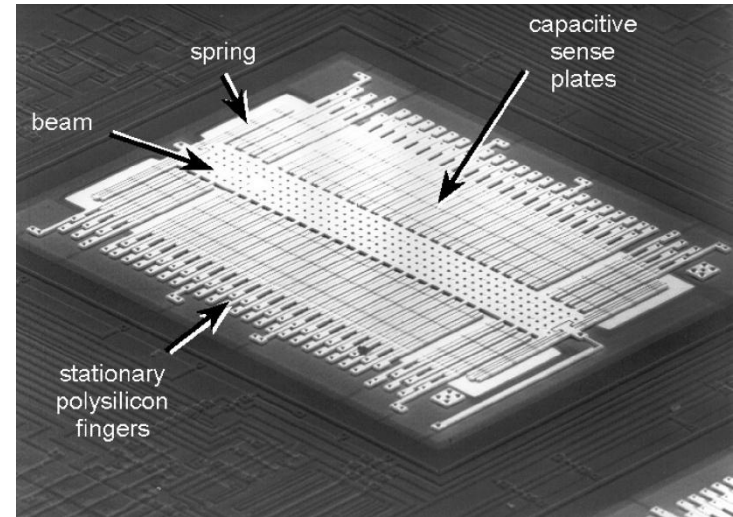
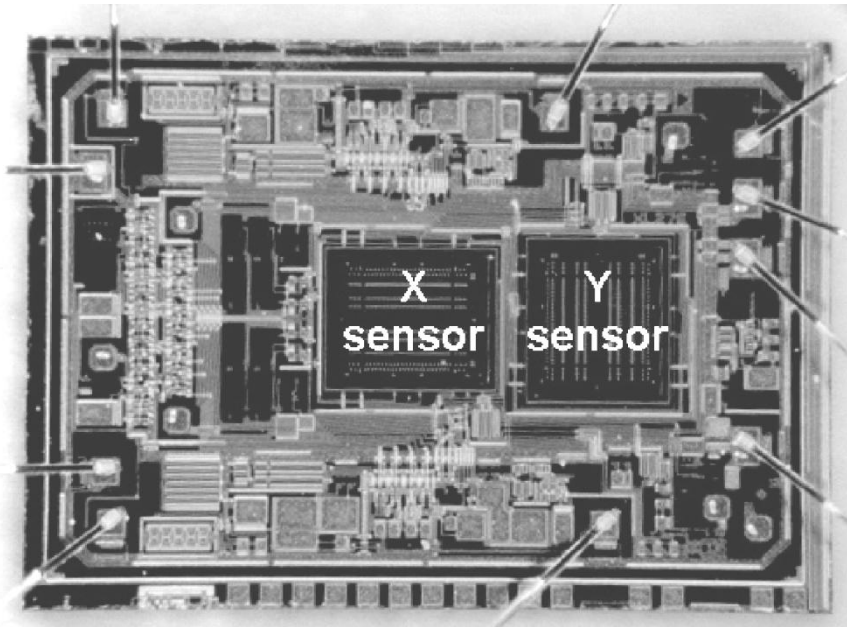
Capacitance $\rightarrow C = \epsilon_r \epsilon_0 \frac{A}{d}$

Single axis capacitive MEMS inertial sensor

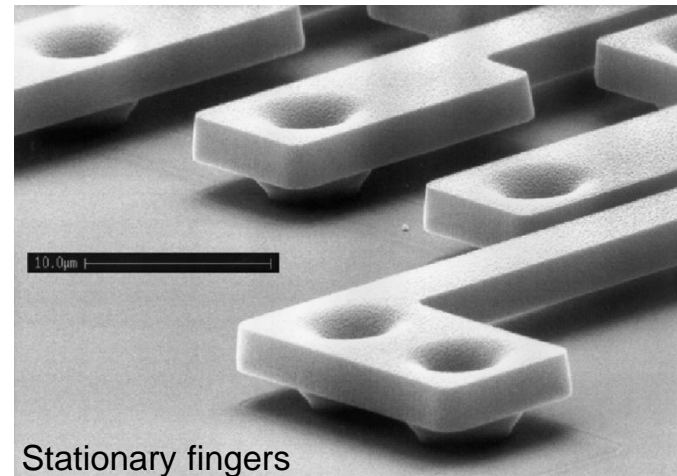
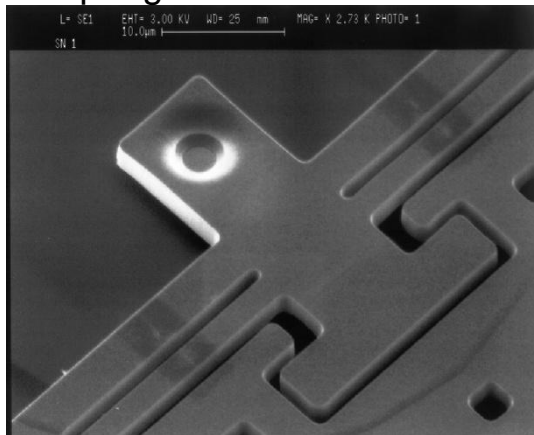


MEMS accelerometers: ADXL 150

Dual-axes accelerometers



Spring attachment: anchor

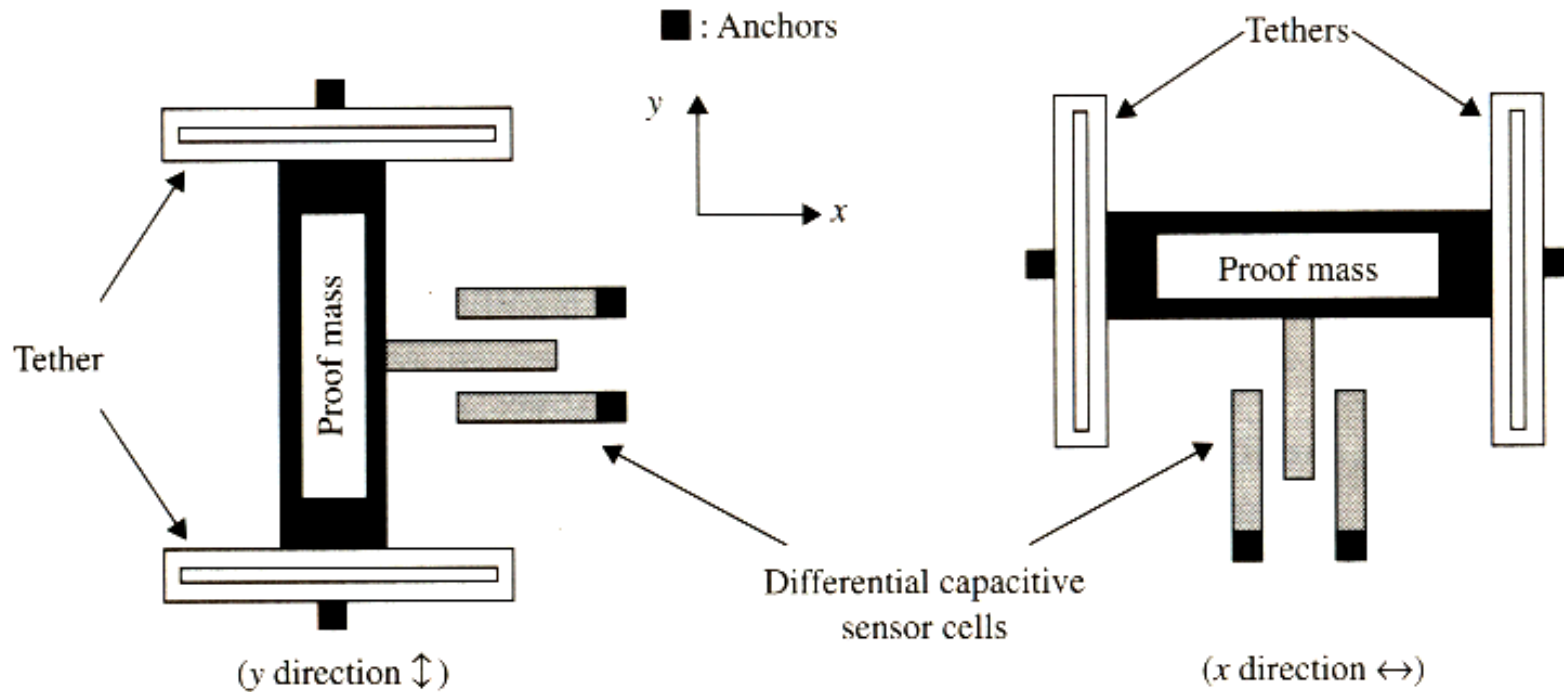


Stationary fingers



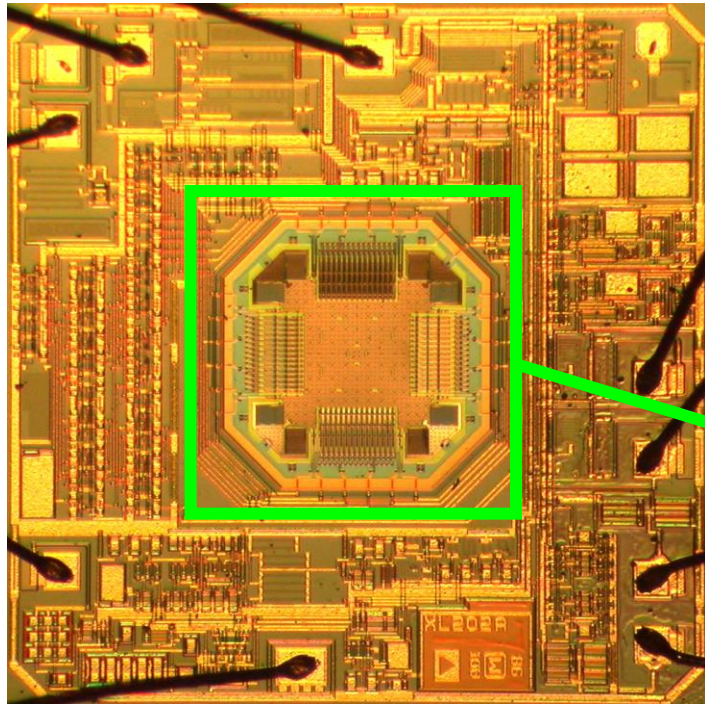
MEMS accelerometers: ADXL 150

Dual-axes accelerometers



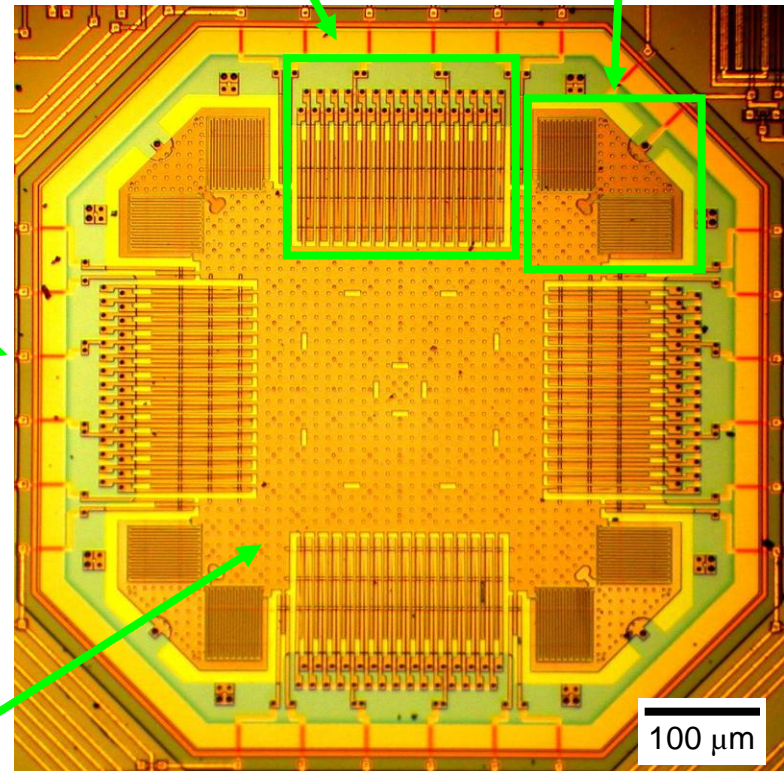
MEMS accelerometers: ADXL 202

Dual-axes accelerometers



Capacitive
combs

Springs



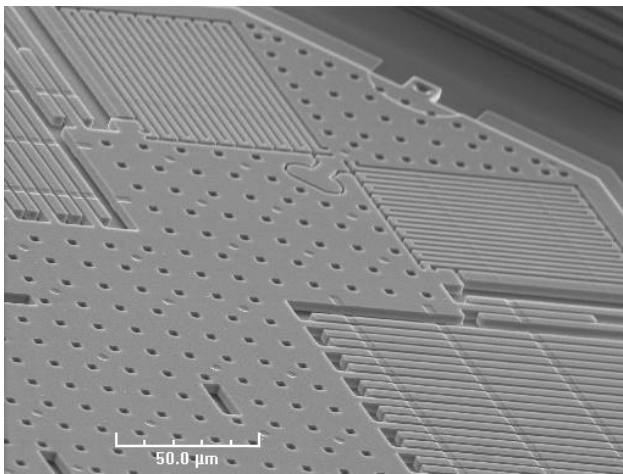
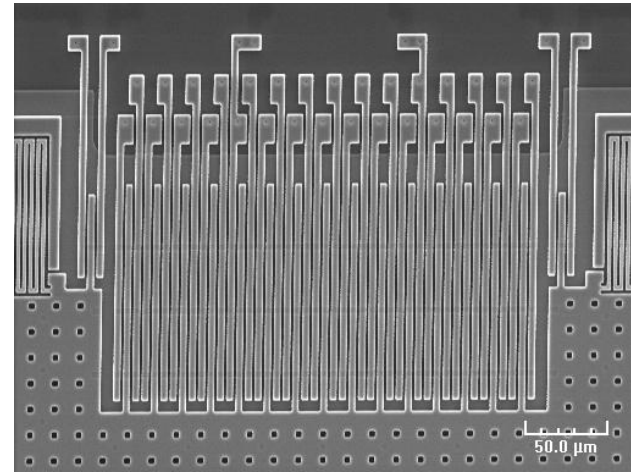
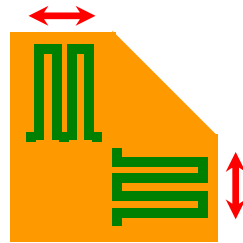
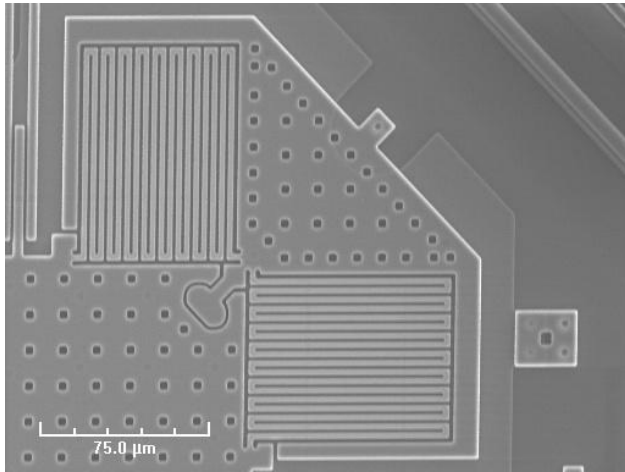
Proof mass

ADXL202 micromechanical sensor

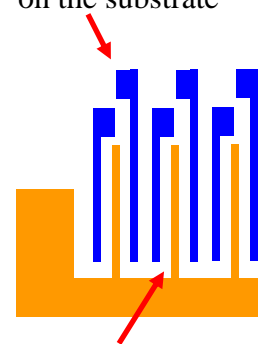


MEMS accelerometers: ADXL 202

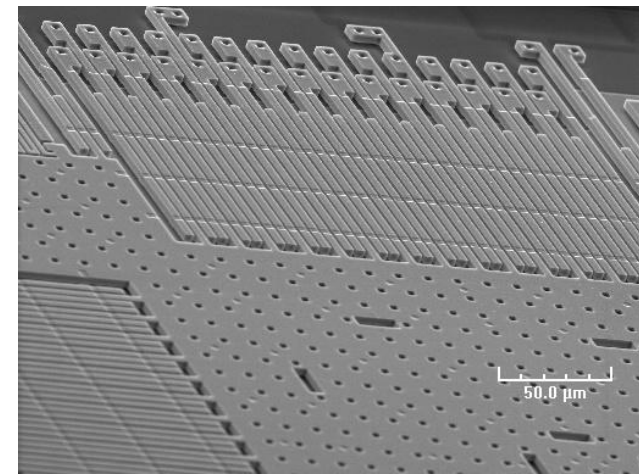
Proof mass has dimensions of $600 \times 600 \times 3 \mu\text{m}^3$



Capacitive electrode on the substrate



Capacitive electrode on the proof mass



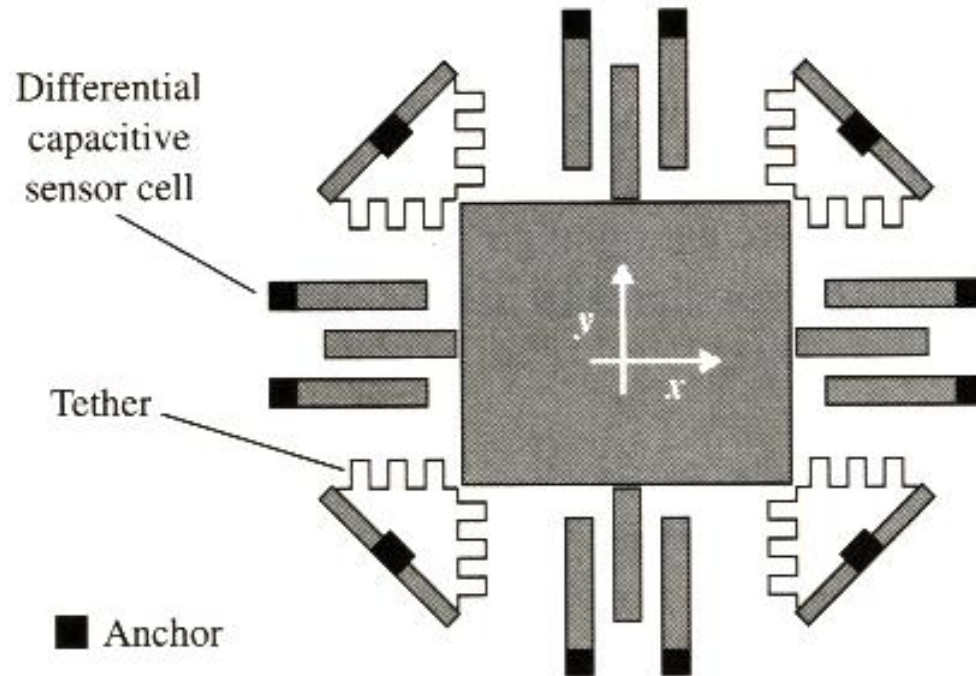
One set of spring elements

One set of capacitive combs



MEMS accelerometers: ADXL 202

Dual-axes accelerometers

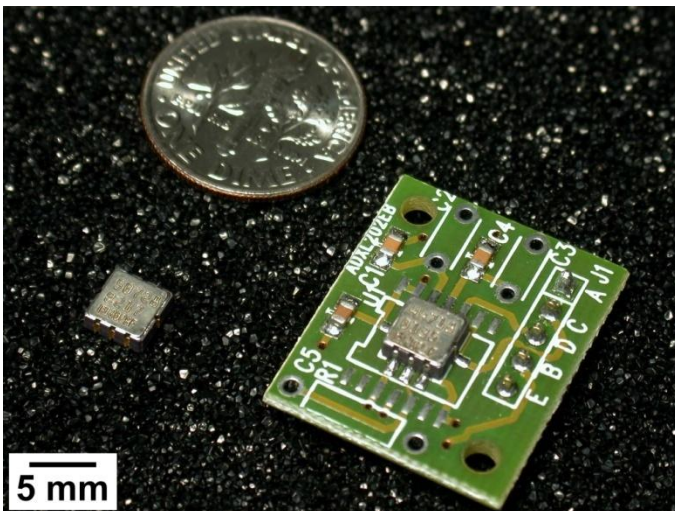


(Courtesy of Analog Devices Inc., Norwood, Massachusetts.)



MEMS accelerometers: ADXL 202

- Provide optimum substitution for typical piezoelectric accelerometers because of their
 - ▲ high resonance frequency
 - ▲ light weight, small size, low power use
- Some properties of the Analog Devices' *ADXL202* dual-axes accelerometer include



ADXL202 packages

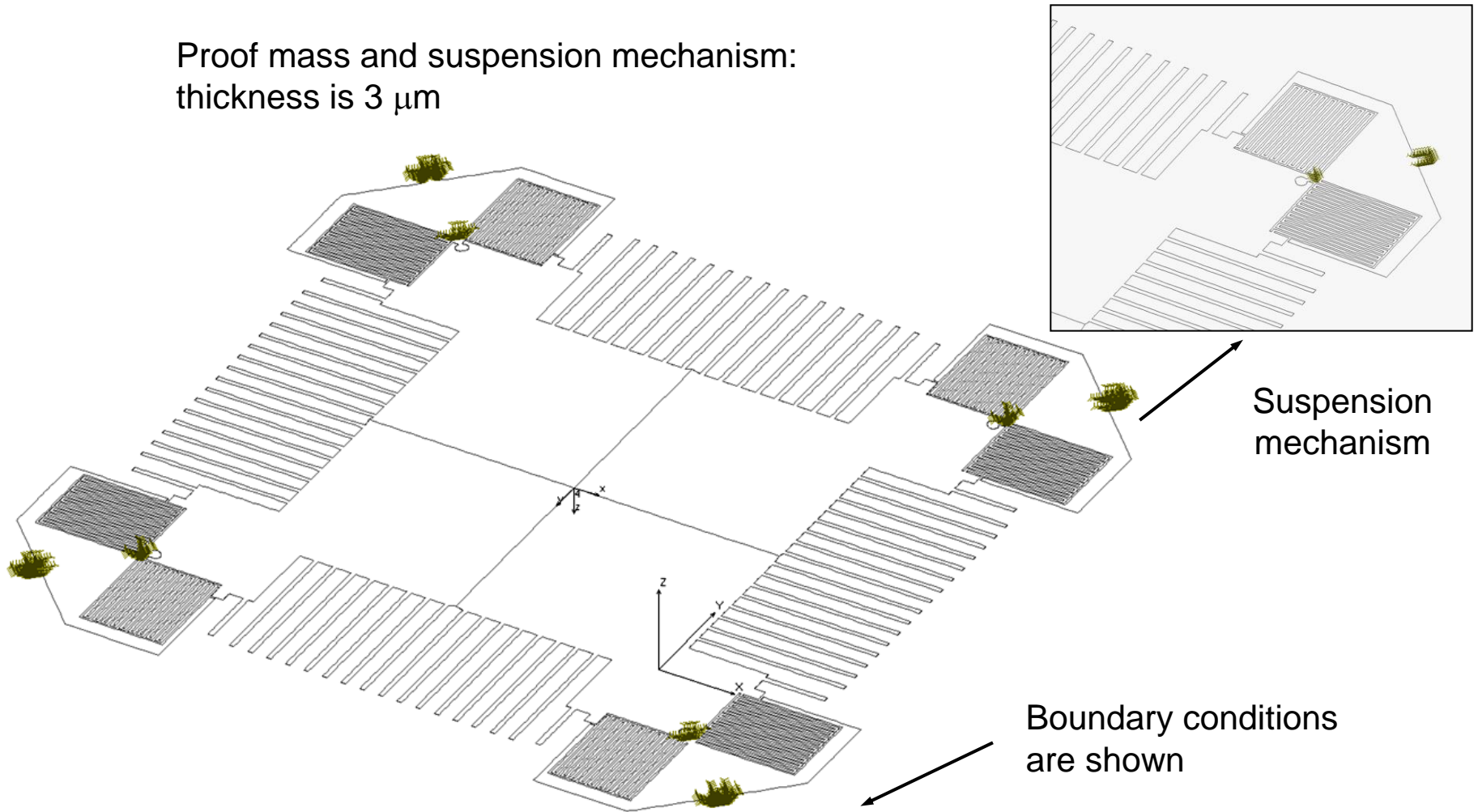
Specifications of Analog Devices ADXL202			
Measurement range	± 2 g	Operating voltage	3.0-5.25 V
Sensitivity	312 mV/ g	Mass	160 ± 10 mgr
Resonance frequency	10 kHz	Operating temperature	$[-40,85]$ °C



MEMS accelerometers: ADXL 202

Modal analysis using FEM (free-vibrations)

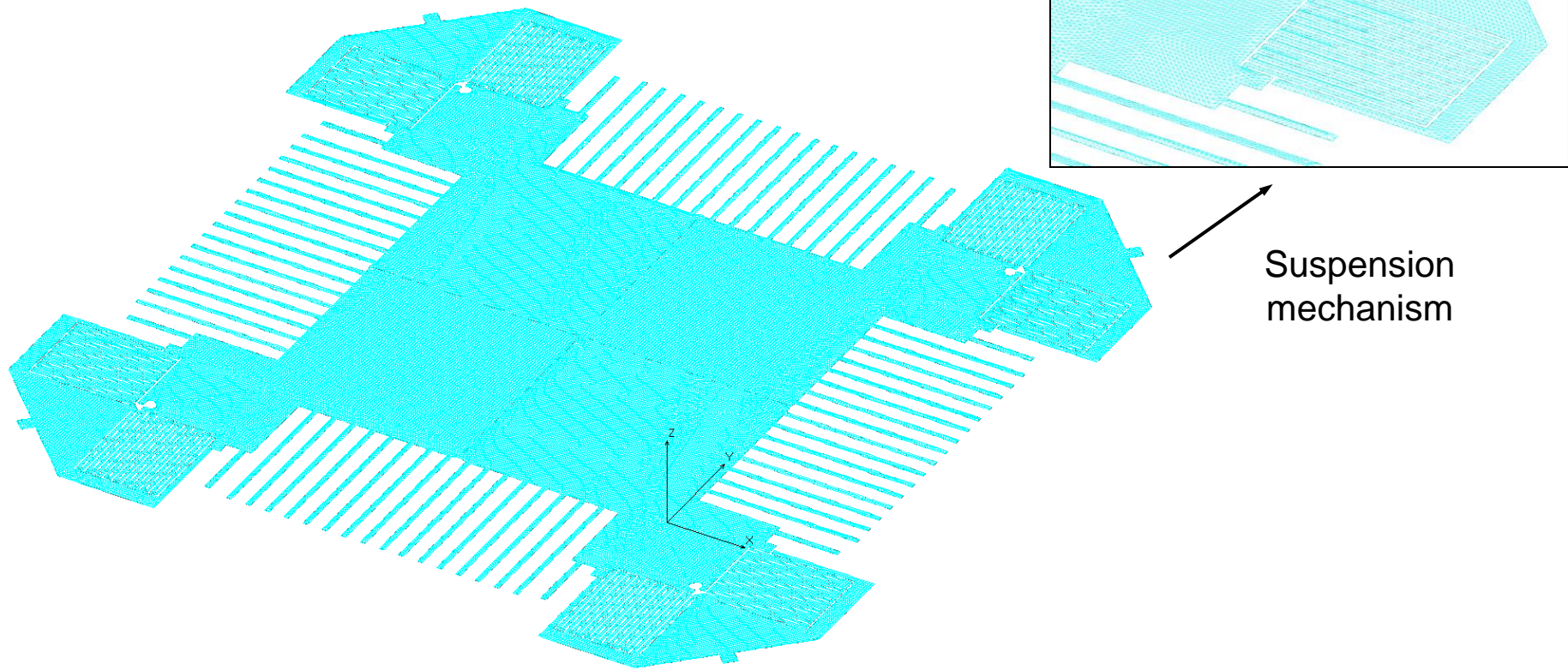
Proof mass and suspension mechanism:
thickness is $3\ \mu\text{m}$



MEMS accelerometers: ADXL 202

Modal analysis using FEM (free-vibrations)

Proof mass and suspension mechanism: mesh (domain discretization), 109,772 3-shell elements



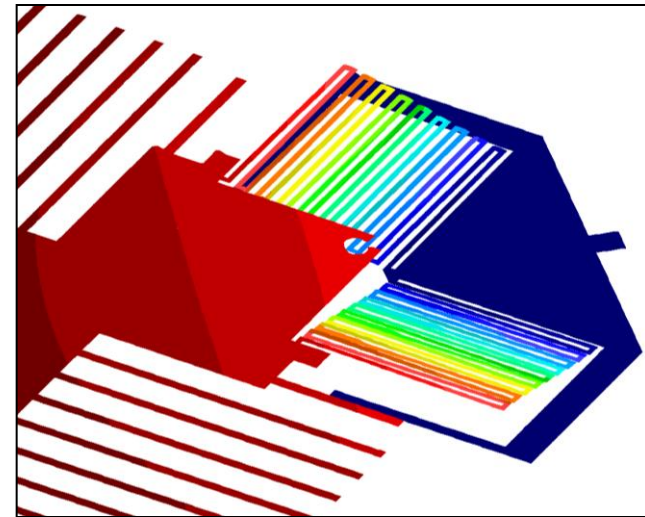
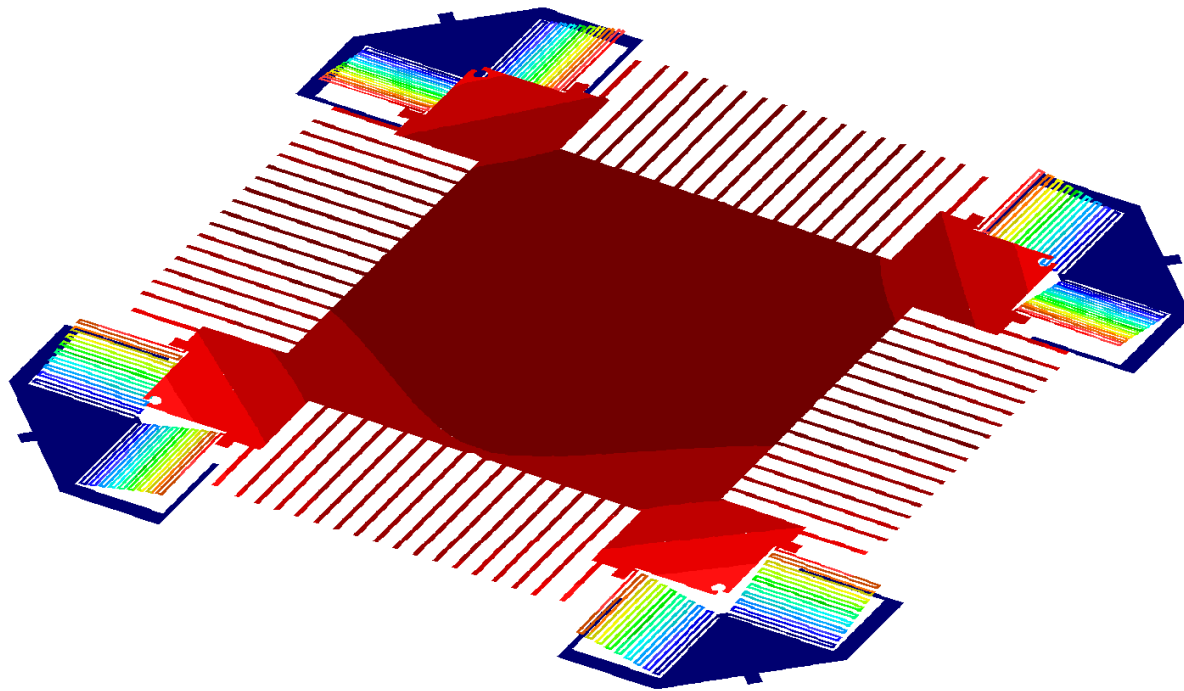
MEMS accelerometers: ADXL 202

Modal analysis using FEM (free-vibrations)

First mode of vibration: predicted at 10.8 kHz

Material properties utilized:

- 160 Gpa
- 2.33 gr/cm³



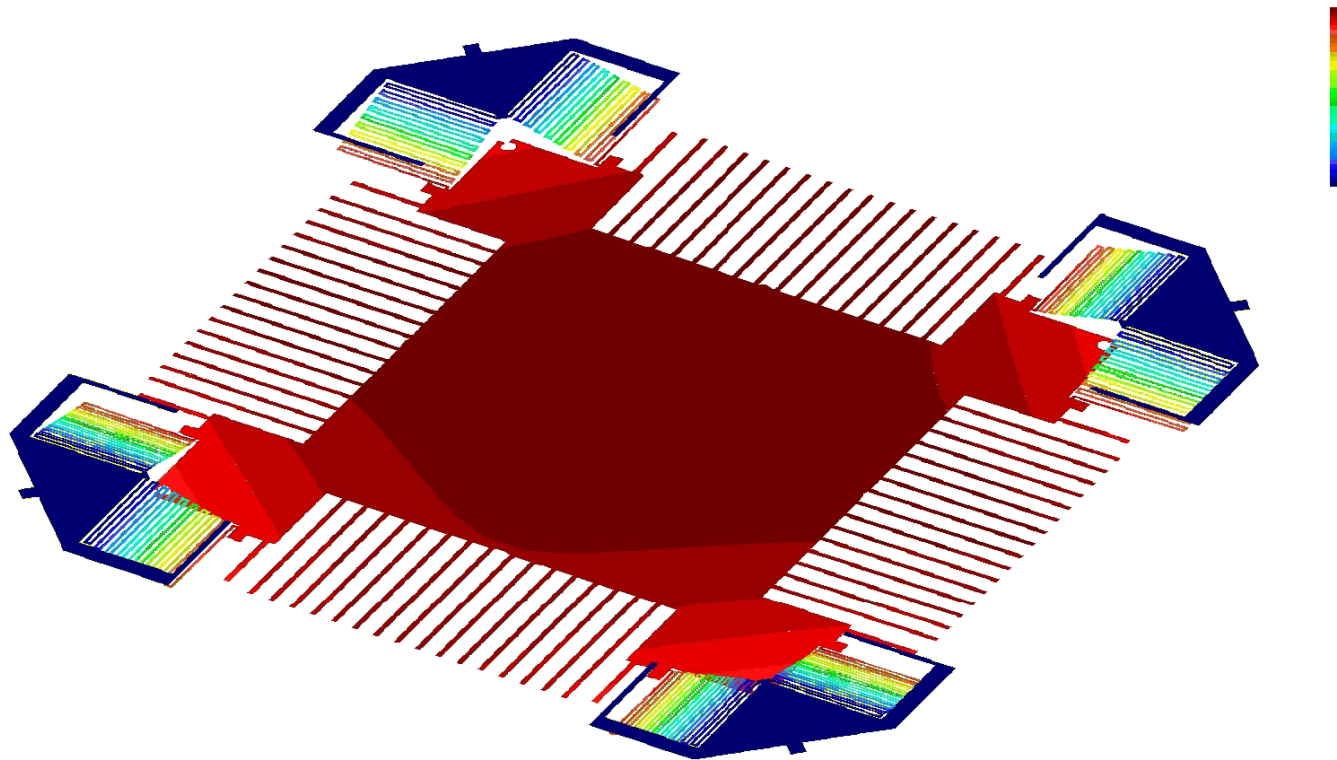
Suspension mechanism



MEMS accelerometers: ADXL 202

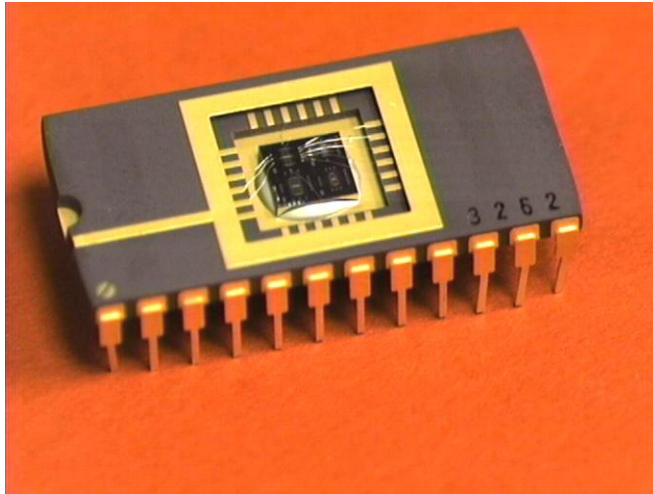
Modal analysis using FEM (free-vibrations)

Animation of the first mode of vibration: predicted at 10.8 kHz

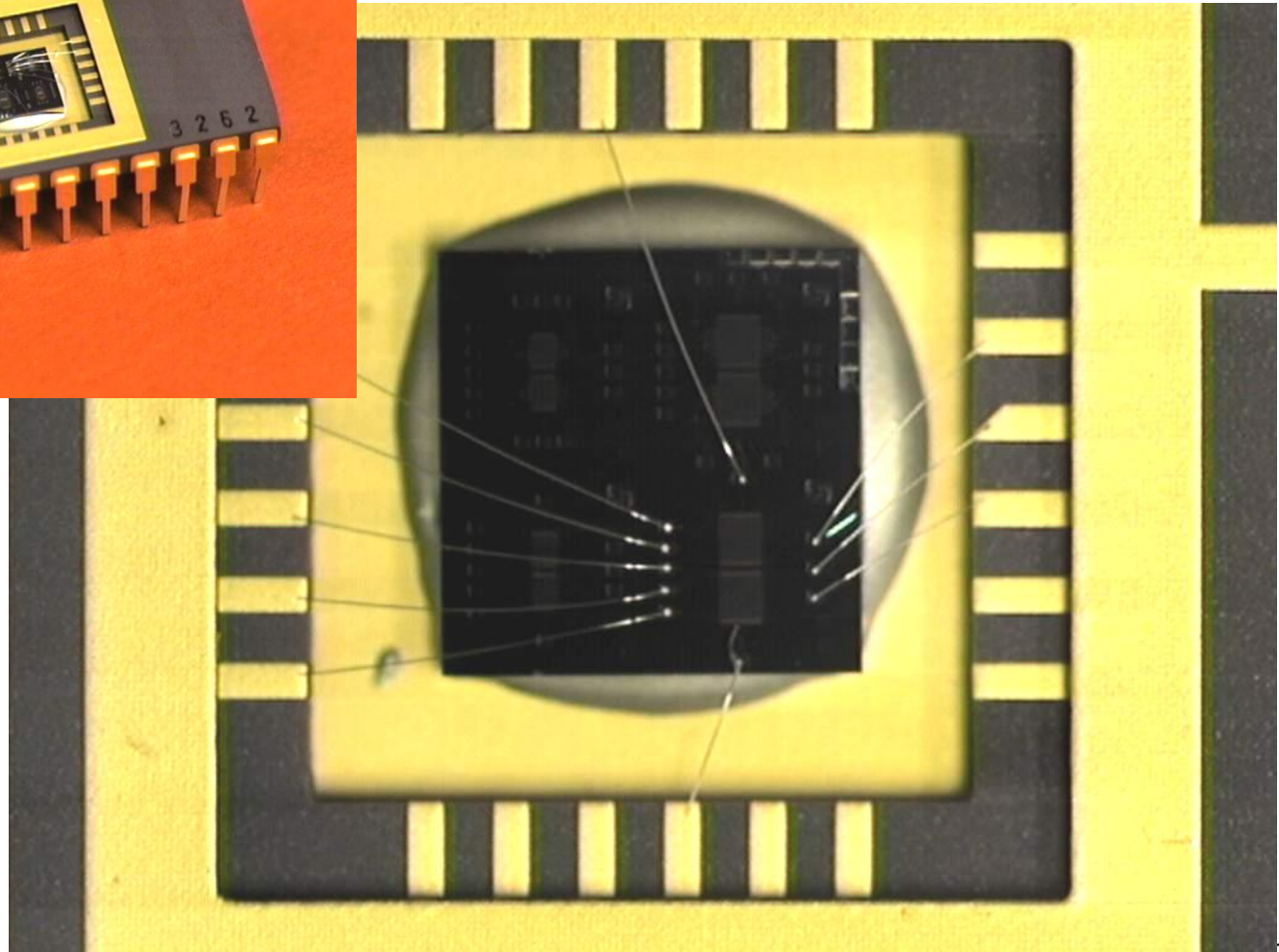


MEMS gyroscopes: packages

SNL - Sandia National Laboratories

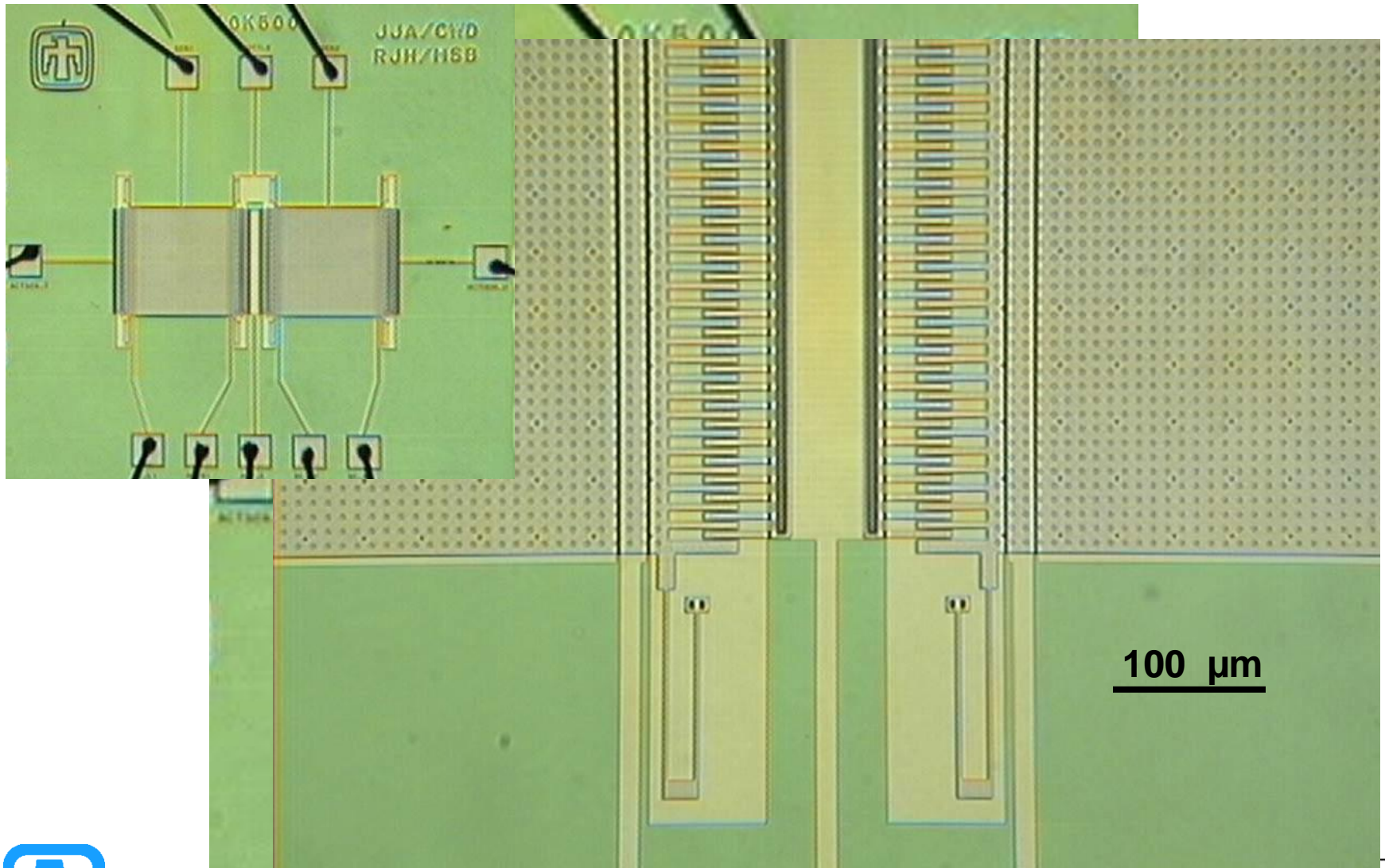


Electronic packages



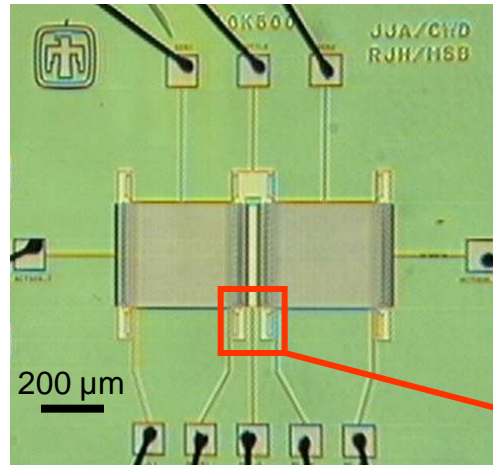
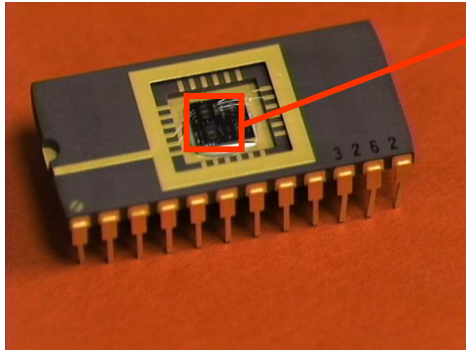
MEMS gyroscopes: packages

SNL - Sandia National Laboratories



MEMS gyroscopes: SNL

Microgyro package



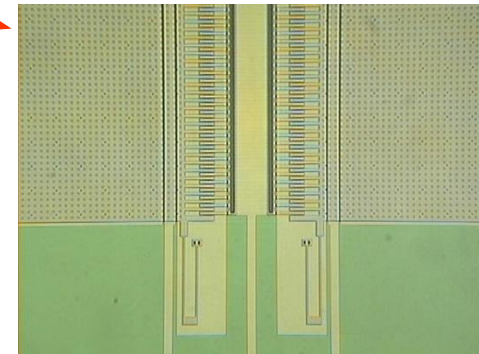
10 kHz microgyro: 300 μm × 300 μm shuttles, configured as a differential pair

Relative motion analysis:

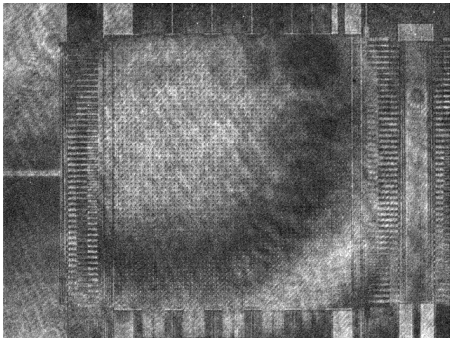
$$\bar{r}_B = \bar{r}_A + \bar{r}_{B/A}$$

Acceleration:

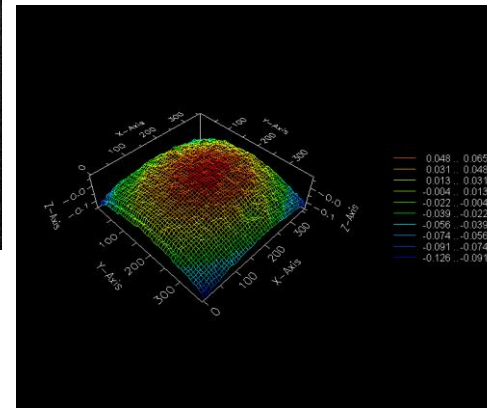
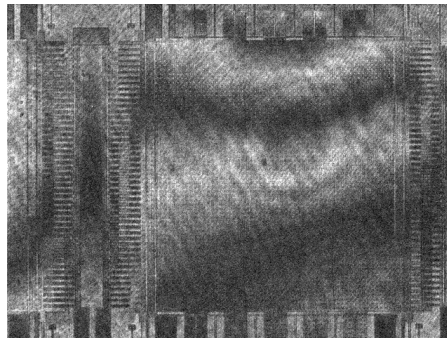
$$\bar{a}_B = \bar{a}_A + \bar{\Omega} \times \bar{r}_{B/A} + \bar{\Omega} \times (\bar{\Omega} \times \bar{r}_{B/A}) + 2\bar{\Omega} \times (\dot{\bar{r}}_{B/A})_{xyz} + (\bar{a}_{B/A})_{xyz}$$



Left shuttle



Right shuttle



OEHM images and deformations of the microgyro operating at 10 kHz: 217 nm max



Reading assignment

- **Beckwith:** Ch. 6, 17, Appendix B
- **Bishop:** Ch. 11

References:

- J.P.Holman, *Experimental methods for engineers*, McGraw-Hill, 1989
- T. G. Beckwith, R. D. Marangoni, and J. H. Lienhard, *Mechanical Measurements*, 5th ed., Addison-Wesley, 1995
- C. Furlong, *MEMS: introduction and applications*, Course notes on MEMS, ISTFA, 2004, Worcester, MA
- Sandia National Laboratories. <http://www.sandia.gov>



Homework assignment: Handout-M

- Beckwith: 17.1
- Bishop: Section 11.7.1

